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Kind regards,
Team Nexperia

## DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC


## HEF40373B MSI <br> Octal transparent latch with 3-state outputs

Product specification
File under Integrated Circuits, IC04

PHILIPS

## Octal transparent latch with 3-state outputs

## DESCRIPTION

The HEF40373B is an 8-bit transparent latch with 3-state buffered outputs. The output stages have high current output capability suitable for driving highly capacitive loads. The latch outputs follow the data inputs when the latch enable ( E ) is HIGH. When E is LOW, the data that meets the set-up times is latched. The 3-state outputs are controlled by the output enable input $\overline{\mathrm{EO}}$. A HIGH on


Fig. 1 Functional diagram.
$\overline{\mathrm{EO}}$ causes the outputs to assume a high impedance OFF-state. The device features hysteresis on the E input to improve noise rejection.
Schmitt-trigger action in the E input makes the circuit highly tolerant to slower input rise and fall times.

The HEF40373B is pin and functionally compatible with the TTL '373' device.
Supply voltage range: 3 to 15 V .


Fig. 2 Pinning diagram.

PINNING

| $D_{0}$ to $D_{7}$ | data inputs |
| :--- | :--- |
| E | latch enable input <br> $\overline{\mathrm{EO}}$ |
| $\mathrm{O}_{0}$ to $\mathrm{O}_{7}$ | output enable input (active LOW) |
| 3-state buffered outputs |  |

FAMILY DATA, IDD LIMITS category MSI
See Family Specifications


Fig. 4 Logic diagram (one latch).

## FUNCTION TABLE

| OPERATING MODES | INPUTS |  |  | INTERNAL <br> REGISTER | OUTPUTS <br> $\mathbf{O}_{\mathbf{0}}$ TO O O $_{\mathbf{7}}$ |
| :--- | :---: | :---: | :---: | :---: | :---: |
|  | $\overline{\text { EO }}$ | E | $\mathbf{D}_{\mathbf{n}}$ |  | L |
| enable \& read register |  |  |  |  |
|  | L | H | H | H |  |
| latch register \& disable outputs | L | H | H | L | L |
|  | L | L | I | H | H |
|  | L | L | h | L | Z |
|  | H | L | I | H | Z |

## Notes

1. $\mathrm{H}=\mathrm{HIGH}$ state (the more positive voltage)
$\mathrm{h}=$ HIGH state (one set-up time prior to the HIGH-to-LOW enable transition)
L = LOW state (the less positive voltage)
I = LOW state (one set-up time prior to the HIGH-to-LOw enable transition)
$Z=$ high impedance OFF-state

## Octal transparent latch with 3-state outputs

## RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)
See Family Specifications, except for:
D.C. current into any input
D.C. source or sink current into any output

| $\pm I_{1}$ | max. | 10 mA |
| :--- | :--- | ---: |
| $\pm \mathrm{l}_{\mathrm{O}}$ | max. | 25 mA |
| $\pm \mathrm{I}$ | max. | 100 mA |

## DC CHARACTERISTICS

$\mathrm{V}_{\mathrm{SS}}=0 \mathrm{~V}$



Fig. 5 Typical output source current characteristic.

(1) P-channel MOS transistor conducting.
(2) P-channel MOS transistor and bipolar $\mathrm{n}-\mathrm{p}-\mathrm{n}$ transistor conducting.

Fig. 6 Schematic diagram of output stage.

## AC CHARACTERISTICS

$\mathrm{V}_{\mathrm{SS}}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C} ; \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$; input transition times $\leq 20 \mathrm{~ns}$


## AC CHARACTERISTICS

$\mathrm{V}_{\mathrm{SS}}=0 \mathrm{~V} ; \mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$; input transition times $\leq 20 \mathrm{~ns}$

|  | $\begin{gathered} \mathbf{V}_{\mathrm{DD}} \\ \mathbf{V} \end{gathered}$ | TYPICAL FORMULA FOR P ( $\mu \mathrm{W}$ ) |  |
| :---: | :---: | :---: | :---: |
| Dynamic power dissipation per package (P) | $\begin{array}{r} 5 \\ 10 \\ 15 \end{array}$ | $\begin{array}{r} 3325 f_{i}+\sum\left(f_{o} C_{L}\right) \times V_{D D}{ }^{2} \\ 14200 f_{i}+\sum\left(f_{0} C_{L}\right) \times V_{D D^{2}} \\ 37425 f_{i}+\sum\left(f_{o} C_{L}\right) \times V_{D D^{2}} \end{array}$ | where <br> $\mathrm{f}_{\mathrm{i}}=$ input freq. $(\mathrm{MHz})$ <br> $\mathrm{f}_{\mathrm{o}}=$ output freq. (MHz) <br> $\mathrm{C}_{\mathrm{L}}$ = load capacitance (pF) <br> $\sum\left(\mathrm{f}_{\mathrm{O}} \mathrm{C}_{\mathrm{L}}\right)=$ sum of outputs <br> $\mathrm{V}_{\mathrm{DD}}=$ supply voltage ( V ) |



Fig. 7 Output transition times as a function of the load capacitance. .

